



GL12N65FA9R

GL Silicon N-Channel Power MOSFET

General Description

GL12N65FA9R, the silicon N-channel Enhanced VDMOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.

Features

- Fast Switching
- ESD Improved Capability
- Low ON Resistance(Typical Data:0.58Ω)
- Low Gate Charge (Typical Data:40nC)
- Low Reverse transfer capacitances(Typical:9.5pF)
- 100% Single Pulse avalanche energy Test

Applications

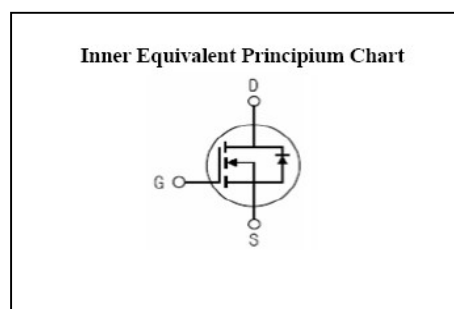
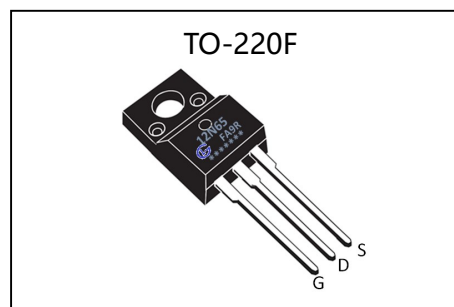
- Power switch circuit of adaptor and charger

Absolute (T_c= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DSS}	Drain-to-Source Voltage	650	V
I _D	Continuous Drain Current	12	A
	Continuous Drain Current T _C = 100 °C	7.5	A
I _{DM} ^{a1}	Pulsed Drain Current	48	A
V _{GS}	Gate-to-Source Voltage	±30	V
E _{AS} ^{a2}	Single Pulse Avalanche Energy	550	mJ
dv/dt ^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P _D	Power Dissipation	55	W
	Derating Factor above 25°C	0.44	W/°C
T _J , T _{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C
T _L	Maximum Temperature for Soldering	300	°C

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device

V _{DSS} (T _C =150°C)	650	V
I _D	12	A
P _D (T _C =25°C)	55	W
R _{DS(ON)MAX}	0.65	Ω





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Electrical Characteristics (Tc= 25°C unless otherwise specified)

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	650	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A, \text{Reference } 25^\circ C$	--	0.74	--	V/°C
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=650V, V_{GS}=0V, T_a=25^\circ C$	--	--	1	μA
		$V_{DS}=520V, V_{GS}=0V, T_a=125^\circ C$	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=6A$	--	0.58	0.65	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	--	4.0	V
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	$V_{DS}=15V, I_D=6.0A$	--	12	--	S
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V$ $f=1.0MHz$	--	1993	--	pF
C_{oss}	Output Capacitance		--	160	--	
C_{rss}	Reverse Transfer Capacitance		--	9.5	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=12.0A, V_{DD}=325V$ $V_{GS}=10V, R_g=10\Omega$	--	28	--	ns
t_r	Rise Time		--	26	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	64	--	
t_f	Fall Time		--	45	--	
Q_g	Total Gate Charge	$I_D=12.0A, V_{DD}=325V$ $V_{GS}=10V$	--	34	--	nC
Q_{gs}	Gate to Source Charge		--	10	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	14	--	



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Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	12	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	48	A
V_{SD}	Diode Forward Voltage	$I_S = 12.0A, V_{GS} = 0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S = 12.0A, T_J = 25^\circ C$	--	386	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100A/us, V_{GS} = 0V$	--	1600	--	nC
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

Thermal Characteristics

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	2.98	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L = 10.0mH, I_D = 11.8A$, Start $T_J = 25^\circ C$

^{a3}: $I_{SD} = 12A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}$, Start $T_J = 25^\circ C$

Characteristics Curves

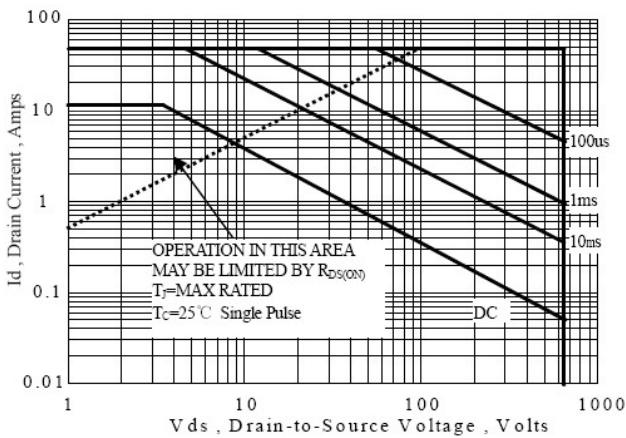


Figure 1 Maximum Forward Bias Safe Operating Area

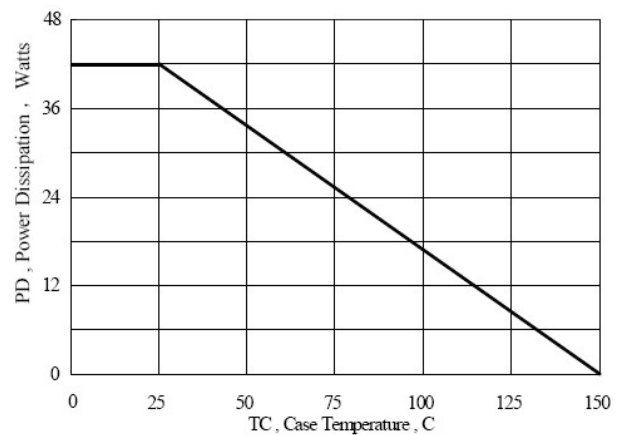


Figure 2 Maximum Power Dissipation vs Case Temperature

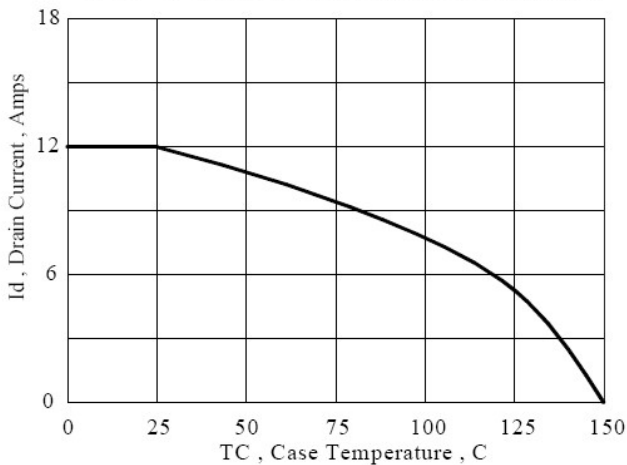


Figure 3 Maximum Continuous Drain Current vs Case Temperature

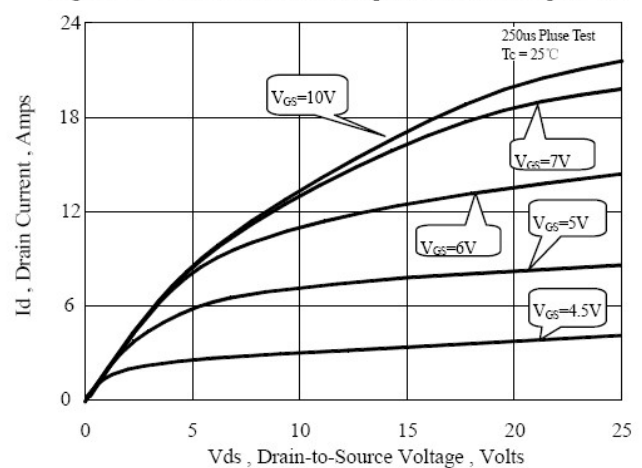


Figure 4 Typical Output Characteristics

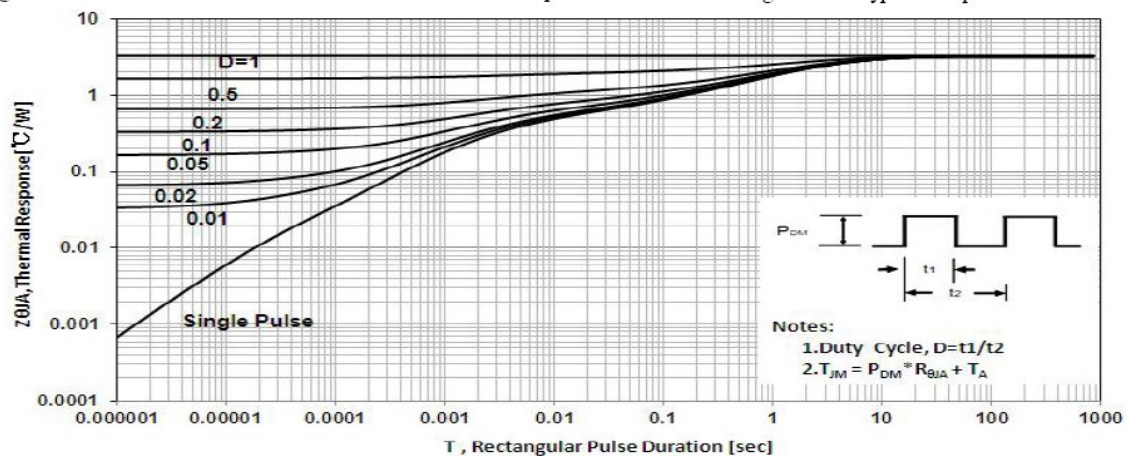


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

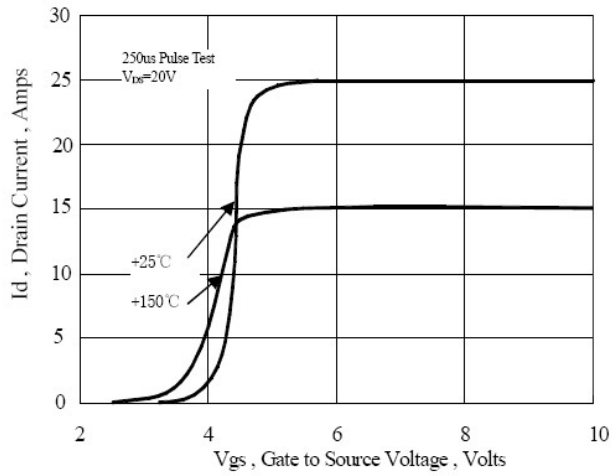


Figure 6 Typical Transfer Characteristics

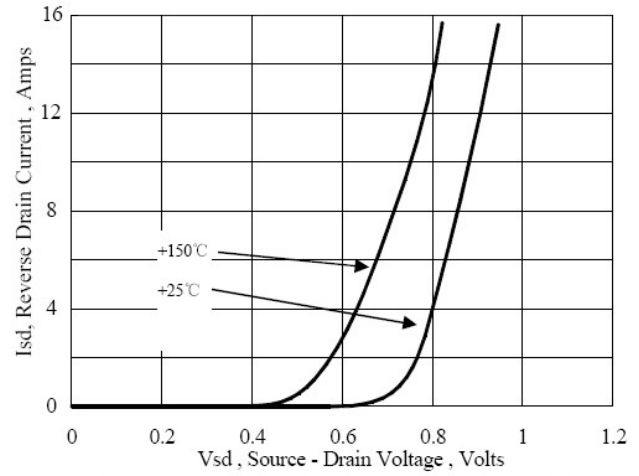


Figure 7 Typical Body Diode Transfer Characteristics

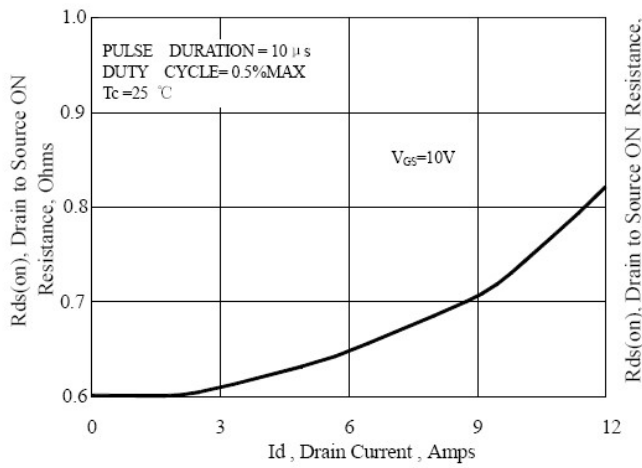


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

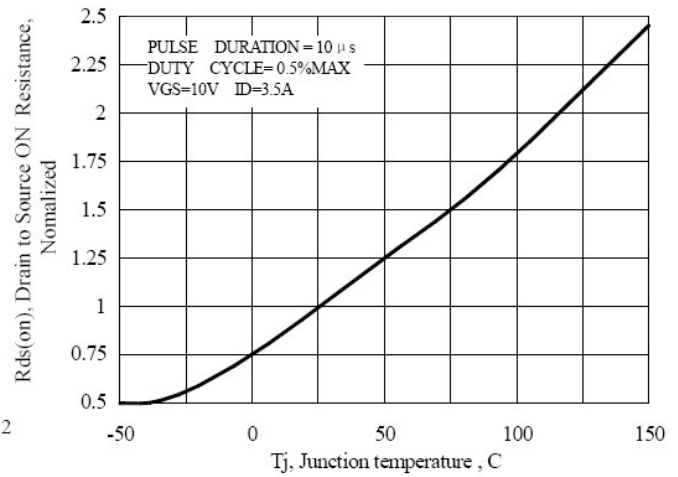


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

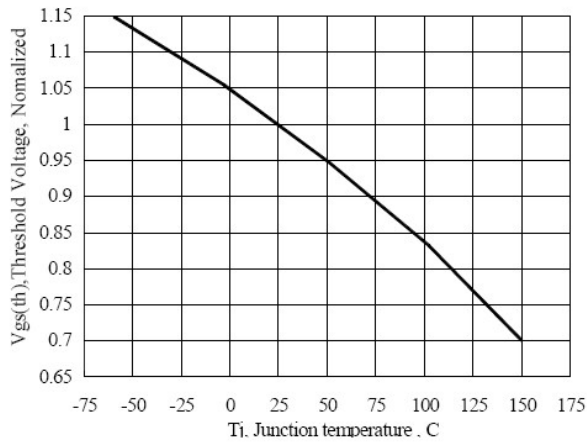


Figure 10 Typical Theshold Voltage vs Junction Temperature

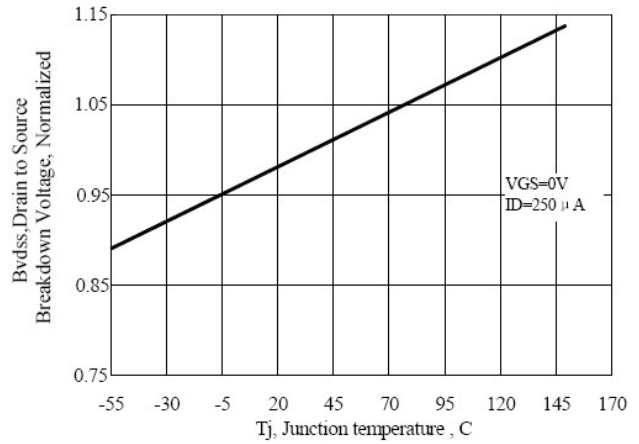


Figure 11 Typical Breakdown Voltage vs Junction Temperature

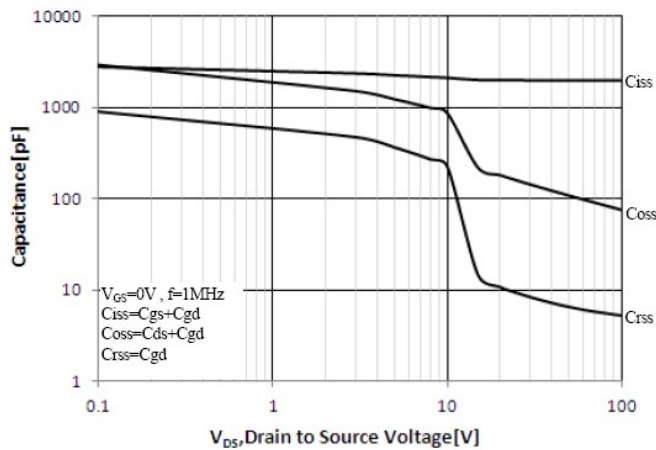


Figure 12 Typical Capacitance vs Drain to Source Voltage

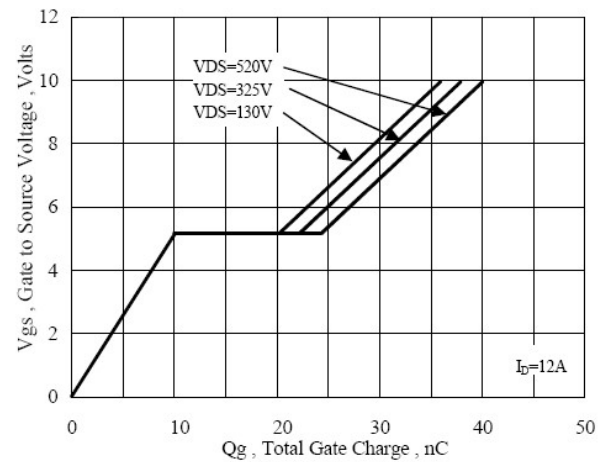


Figure 13 Typical Gate Charge vs Gate to Source Voltage